

20 V, 4.3 A NPN low VCEsat transistor

20 September 2024

Product data sheet

1. General description

NPN low V_{CEsat} transistor in a SOT23 small Surface-Mounted Device (SMD) plastic package. PNP complement: PBSS4021PT

2. Features and benefits

- Very low collector-emitter saturation voltage V_{CEsat}
- High collector current capability ${\sf I}_{\sf C}$ and ${\sf I}_{\sf CM}$
- + High collector current gain (h_{FE}) at high I_C
- High energy efficiency due to less heat generation
- Smaller required Printed-Circuit Board (PCB) area than for conventional transistors
- AEC-Q101 qualified

3. Applications

- Loadswitch
- Battery-driven devices
- Power management
- Charging circuits
- Power switches (e.g. motors, fans)

4. Quick reference data

Table 1. Quick reference data							
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base		-	-	20	V
I _C	collector current			-	-	4.3	A
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	-	8	A
R _{CEsat}	collector-emitter saturation resistance	I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le$ 300 μs; δ ≤ 0.02; T_{amb} = 25 °C		-	32.5	50	mΩ

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5. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	В	base	3	С
2	E	emitter		J
3	С	collector		BK E
			1 2 SOT23	sym021

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
PBSS4021NT	SOT23	plastic, surface-mounted package; 3 terminals; 1.9 mm pitch; 2.9 mm x 1.3 mm x 1 mm body	<u>SOT23</u>		

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS4021NT	%BH

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

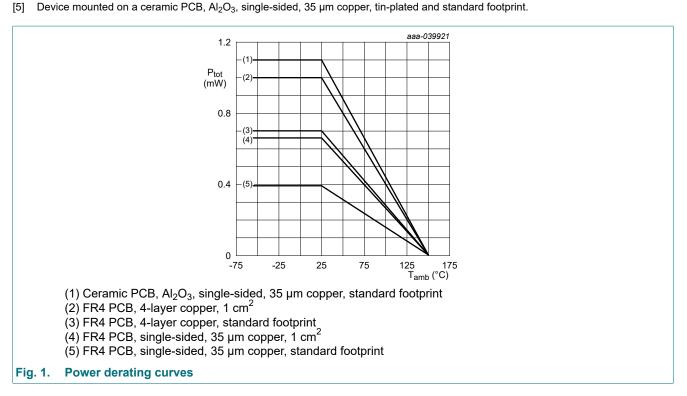
Symbol	Parameter	Conditions		Min	Max	Unit
V _{CBO}	collector-base voltage	open emitter		-	20	V
V _{CEO}	collector-emitter voltage	open base		-	20	V
V _{EBO}	emitter-base voltage	open collector		-	5	V
l _C	collector current			-	4.3	А
I _{CM}	peak collector current	single pulse; t _p ≤ 1 ms		-	8	А
I _B	base current			-	1	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	0.39	W
			[2]	-	0.66	W
			[3]	-	0.7	W
			[4]	-	1	W
			[5]	-	1.1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint.

[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm².



9. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
R _{th(j-a)} thermal resistance from in junction to ambient		in free air [1]	[1]	-	-	320	K/W
	junction to ambient	[2]	-	-	190	K/W	
		[3]	-	-	180	K/W	
		[4]	-	-	125	K/W	
	Ī	[5]	-	-	115	K/W	
R _{th(j-sp)}	thermal resistance from junction to solder point			-	-	62	K/W

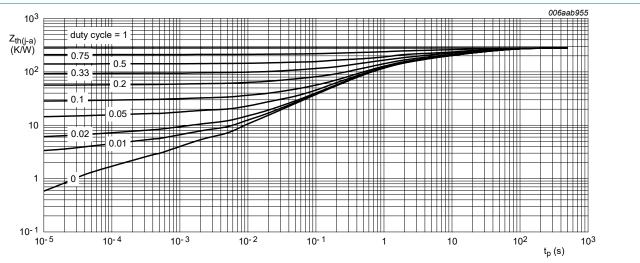
[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint

[2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm²

[3] Device mounted on an FR4 PCB, 4-layer, tin-plated and standard footprint

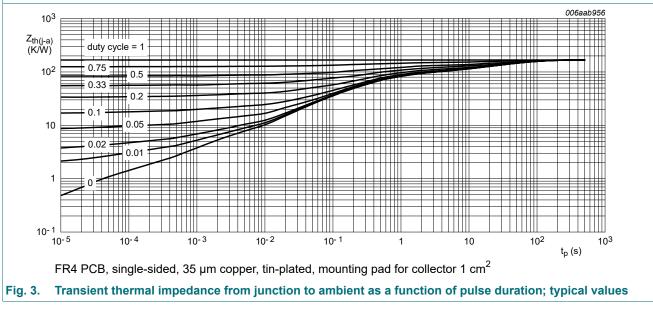
[4] Device mounted on an FR4 PCB, 4-layer, tin-plated, mounting pad for collector 1 cm²

 $[5] \quad \text{Device mounted on a ceramic PCB, } Al_2O_3, \text{ single-sided, } 35 \ \mu\text{m copper, tin-plated and standard footprint}$

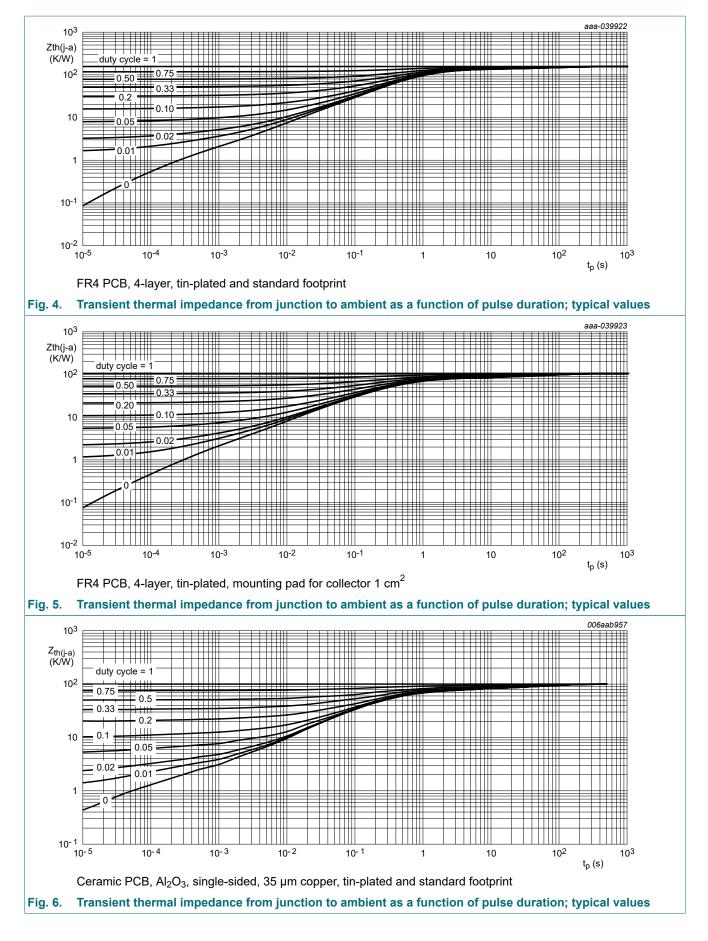


FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint





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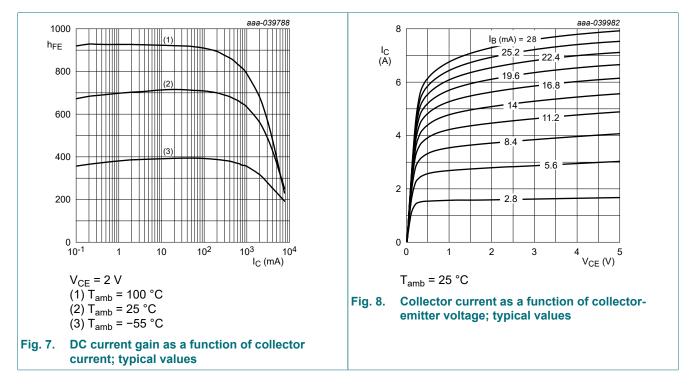


10. Characteristics

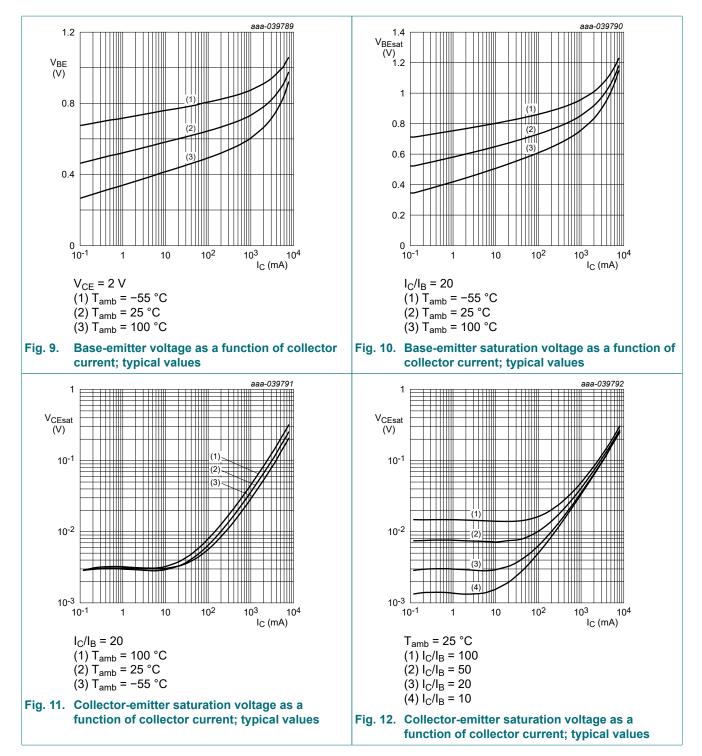
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
V _{(BR)CBO}	collector-base breakdown voltage	I_{C} = 100 µA; I_{E} = 0 A; T_{amb} = 25 °C	20	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	I _C = 10 mA; I _B = 0 A; T _{amb} = 25 °C	20	-	-	V
√ _{(BR)EBO}	emitter-base breakdown voltage	I _E = 100 μA; I _C = 0 A; T _{amb} = 25 °C	5	-	-	V
СВО	collector-base cut-off	V _{CB} = 20 V; I _E = 0 A; T _{amb} = 25 °C	-	-	100	nA
	current	V _{CB} = 20 V; I _E = 0 A; T _j = 150 °C	-	-	50	μA
CES	collector-emitter cut-off current	V _{CE} = 16 V; V _{BE} = 0 V; T _{amb} = 25 °C	-	-	100	nA
EBO	emitter-base cut-off current	V _{EB} = 5 V; I _C = 0 A; T _{amb} = 25 °C	-	-	100	nA
J ^{EE}	DC current gain	V _{CE} = 2 V; I _C = 500 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	300	600	-	
	V_{CE} = 2 V; I _C = 1 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	300	550	-		
	V_{CE} = 2 V; I _C = 2 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	300	500	-		
	V_{CE} = 2 V; I _C = 4 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	150	400	-		
		V_{CE} = 2 V; I _C = 6 A; pulsed; t _p ≤ 300 µs; δ ≤ 0.02; T _{amb} = 25 °C	100	300	-	
√ _{CEsat}	collector-emitter saturation voltage	I _C = 1 A; I _B = 10 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	55	75	mV
		I _C = 1 A; I _B = 50 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	40	60	mV
		I _C = 2 A; I _B = 40 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	80	120	mV
		I _C = 4 A; I _B = 40 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	160	265	mV
		I _C = 4 A; I _B = 200 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	135	220	mV
		I_{C} = 4 A; I_{B} = 400 mA; pulsed; $t_{p} \le$	-	130	200	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	32.5	50	mΩ
/ _{BEsat}	base-emitter saturation voltage	I _C = 1 A; I _B = 100 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	0.87	1.05	V
		I _C = 4 A; I _B = 400 mA; pulsed; t _p ≤ 300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-	1.08	1.25	V
/ _{BE}	base-emitter voltage	V_{CE} = 2 V; I _C = 2 A; pulsed; t _p ≤ 300 µs; $\delta \le 0.02$; T _{amb} = 25 °C	-	0.76	0.9	V

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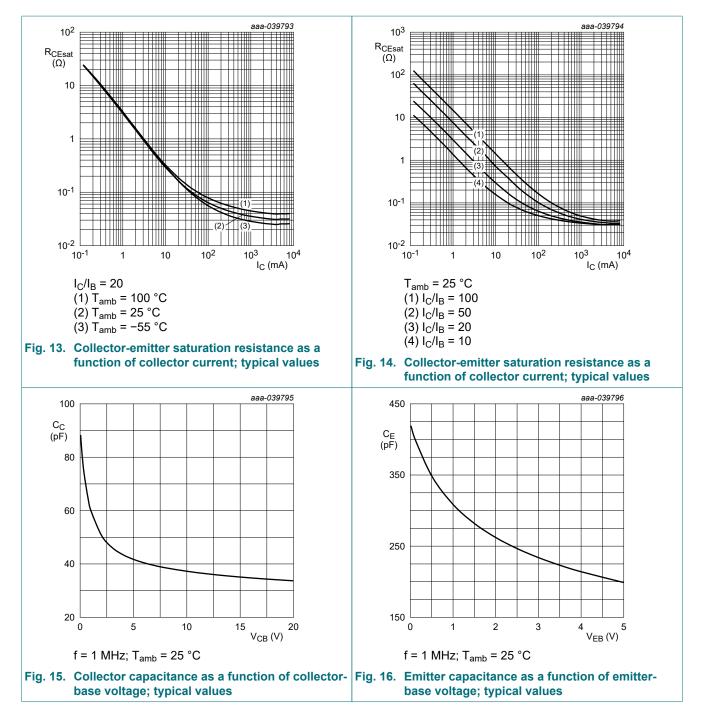
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
t _d	delay time	V _{CC} = 12.5 V; I _C = 1 A; I _{Bon} = 50 mA;	-	20	-	ns
t _r	rise time	I _{Boff} = -50 mA; T _{amb} = 25 °C	-	30	-	ns
t _{on}	turn-on time		-	50	-	ns
ts	storage time		-	355	-	ns
t _f	fall time] [-	70	-	ns
t _{off}	turn-off time		-	425	-	ns
f _T	transition frequency	V_{CE} = 10 V; I _C = 100 mA; f = 100 MHz; T _{amb} = 25 °C	-	150	-	MHz
C _c	collector capacitance	V_{CB} = 10 V; I _E = 0 A; i _e = 0 A; f = 1 MHz; T _{amb} = 25 °C	-	36	-	pF



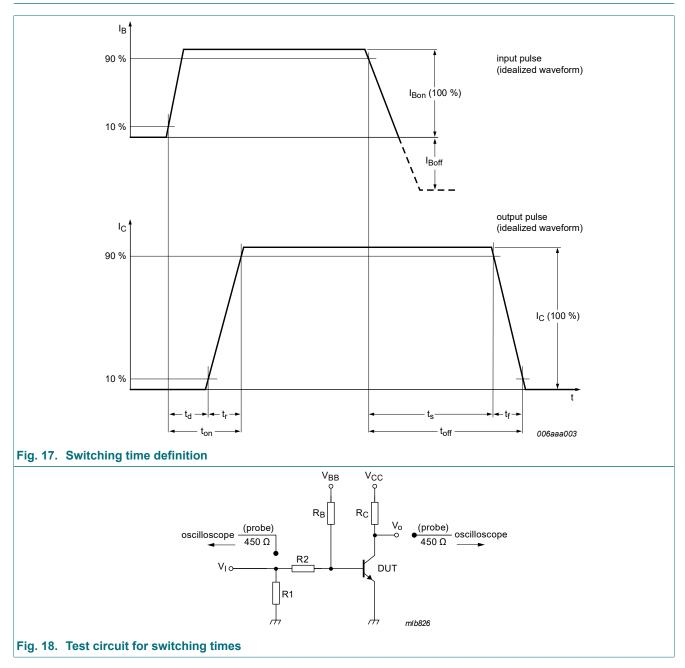
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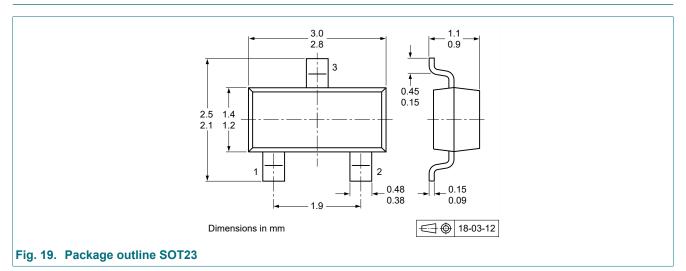
11. Test information



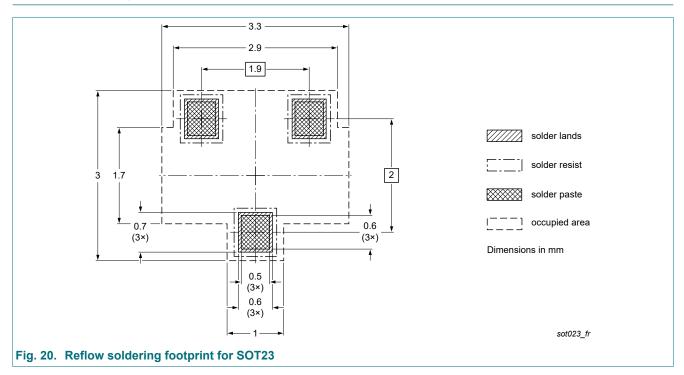
Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

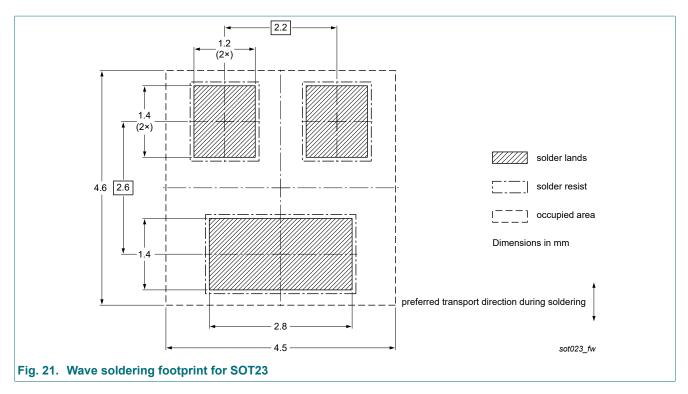
12. Package outline



13. Soldering



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PBSS4021NT

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14. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
PBSS4021NT v.3	20240920	Product data sheet	-	PBSS4021NT v.2
Modifications:	New graphics a	dded, graphs updated and v	alues changed.	
PBSS4021NT v.2	20240207	Product data sheet	-	PBSS4021NT v.1
PBSS4021NT v.1	20100131	Product data sheet	-	-

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

 Please consult the most recently issued document before initiating or completing a design.

- [2] The term 'short data sheet' is explained in section "Definitions".
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